Product data sheet

1. General description

The 74AUP2G00 provides dual 2-input NAND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- · High noise immunity
- · Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- · Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- · ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 3A exceeds 5000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power dual 2-input NAND gate

3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range Name Description								
74AUP2G00DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1					
74AUP2G00GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1					
74AUP2G00GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116					
74AUP2G00GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203					
74AUP2G00GX	-40 °C to +125 °C	X2SON8	plastic thermal enhanced extremely thin small outline package; no leads; 8 terminals; body 1.35 × 0.8 × 0.32 mm	SOT1233-2					

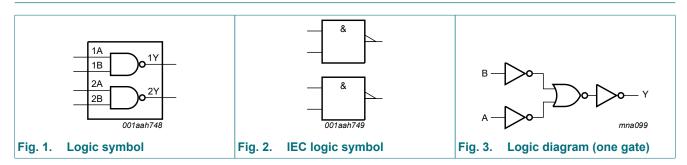
4. Marking

Table 2. Marking codes

Table 21 marking coace						
Marking code[1]						
p00						
p00						
pA						
pA						
pA						

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



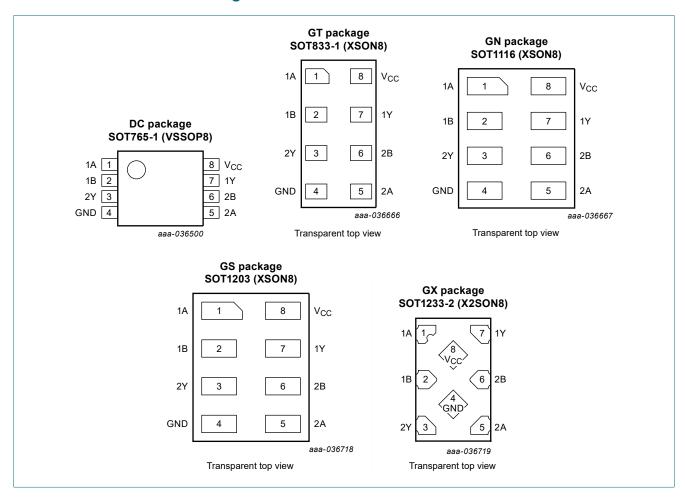
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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

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Symbol	Pin	Description						
1A, 2A	1, 5	data input						
1B, 2B	2, 6	data input						
GND	4	ground (0 V)						
1Y, 2Y	7, 3	data output						
V _{CC}	8	supply voltage						

Low-power dual 2-input NAND gate

7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level.$

Input	Output	
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			-0.5	+4.6	V
VI	input voltage		[1]	-0.5	+4.6	V
Vo	output voltage	Active mode and Power-down mode	[1]	-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
Io	output current	$V_O = 0 V \text{ to } V_{CC}$		-	±20	mA
I _{CC}	supply current			-	+50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C				
		SOT765-1 (VSSOP8) SOT833-1 (XSON8) SOT1116 (XSON8) SOT1203 (XSON8)	[2]	-	250	mW
		SOT1233-2 (X2SON8)	[3]	-	300	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For SOT765-1 (VSSOP8) package: P_{tot} derates linearly with 4.9 mW/K above 99 °C.

For SOT833-1 (XSON8) package: Ptot derates linearly with 3.1 mW/K above 68 °C.

For SOT1116 (XSON8) package: Ptot derates linearly with 4.2 mW/K above 90 °C.

For SOT1203 (XSON8) package: P_{tot} derates linearly with 3.6 mW/K above 81 °C. [3] For SOT1233-2 (X2SON8) package: P_{tot} derates linearly with 7.7 mW/K above 118 °C.

Low-power dual 2-input NAND gate

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 25	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I_{O} = -1.9 mA; V_{CC} = 1.65 V		-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.2	μΑ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	40	μA
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF
T _{amb} = -4	0 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				+
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.5	μA
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_0 = 0 \text{ A};$ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	50	μA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -4	0 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I_{O} = -1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 V$ to 3.6 V; $V_{CC} = 0 V$	-	-	±0.75	μA
Δl _{OFF}	additional power-off leakage current	V ₁ or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	V_{I} = GND or V_{CC} ; I_{O} = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	75	μΑ

^[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

Low-power dual 2-input NAND gate

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5.

Symbol	Parameter	Conditions	T,	_{amb} = 25 °	°C	T _{an}	_{nb} = o +85 °C	T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
C _L = 5 p	F									
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	17.5	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.5	5.3	11.0	2.1	12.2	2.1	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.2	3.6	1.0	4.2	1.0	4.7	ns
C _L = 10	pF									
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	21.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	6.1	13.0	2.2	14.4	2.2	15.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.8	4.3	1.2	4.9	1.2	5.4	ns
C _L = 15	pF									
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	24.5	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	6.9	14.8	3.1	16.5	3.1	18.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	3.2	4.9	1.4	5.7	1.4	6.3	ns
C _L = 30	pF									
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	34.8	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.6	9.2	20.1	4.1	22.6	4.1	24.9	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	4.3	6.5	2.1	7.6	2.1	8.4	ns

Low-power dual 2-input NAND gate

Symbol	Parameter	Conditions	T _{amb} = 25 °C		T _{amb} = -40 °C to +85 °C		T _{amb} = °C -40 °C to +125 °C		Unit				
			Min	Typ[1]	Max	Min	Max	Min	Max				
C _L = 5 p	F, 10 pF, 15 pl	F and 30 pF											
C _{PD}	power dissipation	f_i = 1 MHz; [3] V_I = GND to V_{CC}											
	capacitance	V _{CC} = 0.8 V	-	2.8	-	-	-	-	-	pF			
		V _{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	-	pF			
					V _{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	-	pF
			V _{CC} = 1.65 V to 1.95 V	-	3.0	-	-	-	-	-	pF		
		V _{CC} = 2.3 V to 2.7 V	-	3.4	-	-	-	-	-	pF			
		V _{CC} = 3.0 V to 3.6 V	-	3.9	-	-	-	-	-	pF			

- All typical values are measured at nominal V_{CC}.
- t_{pd} is the same as t_{PLH} and t_{PHL} . C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where:

f_i = input frequency in MHz;

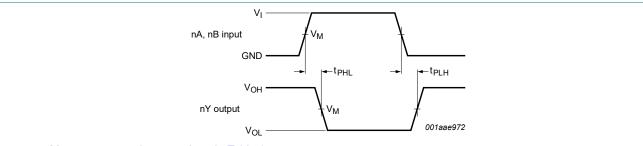
 f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of outputs.

11.1. Waveform and test circuit



Measurement points are given in Table 9.

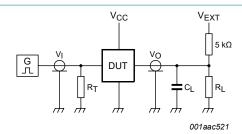
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

The data input (nA or nB) to output (nY) propagation delays Fig. 4.

Table 9. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	VI	$t_r = t_f$
0.8 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns

Low-power dual 2-input NAND gate



Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Zo of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig. 5. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V _{CC}

[1] For measuring enable and disable times R_L = 5 k Ω . For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

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12. Package outline

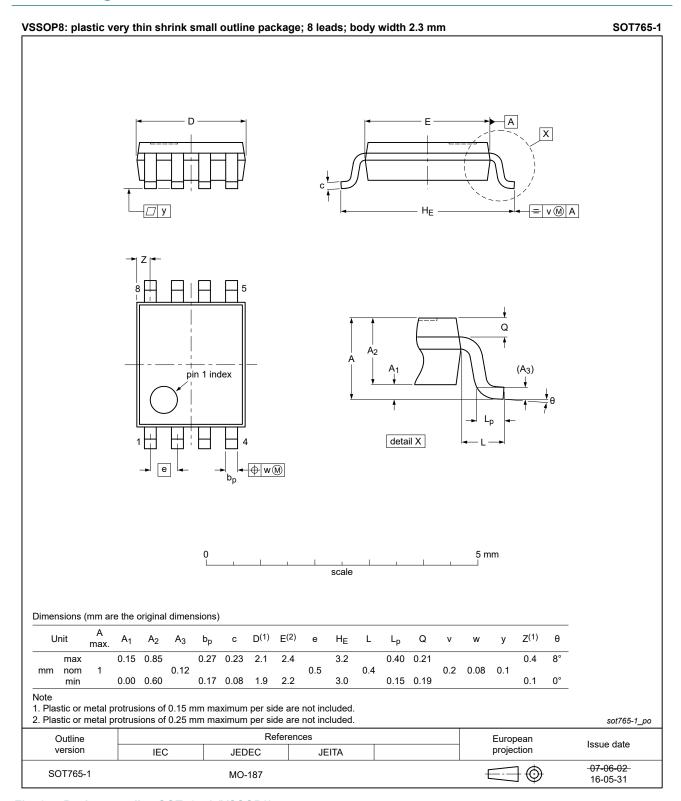


Fig. 6. Package outline SOT765-1 (VSSOP8)

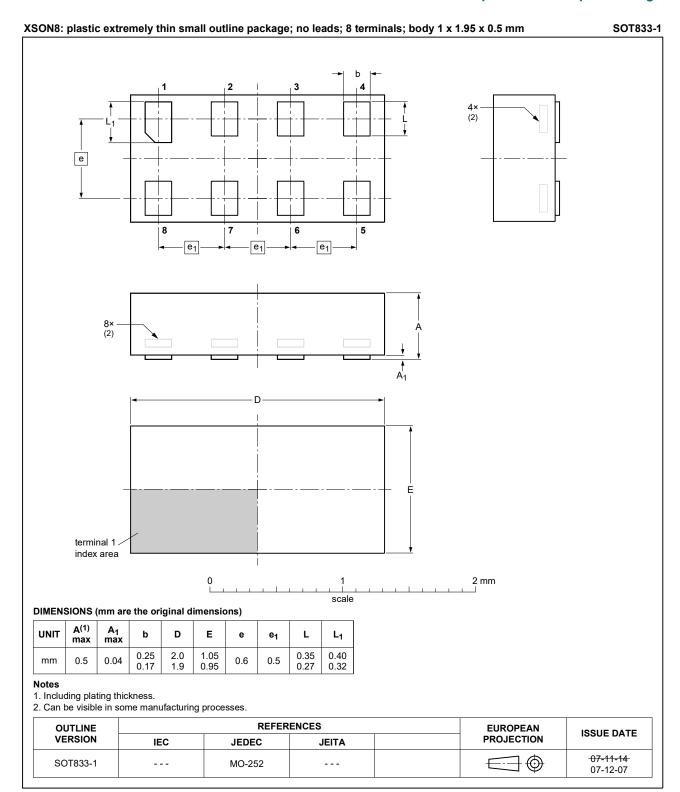


Fig. 7. Package outline SOT833-1 (XSON8)

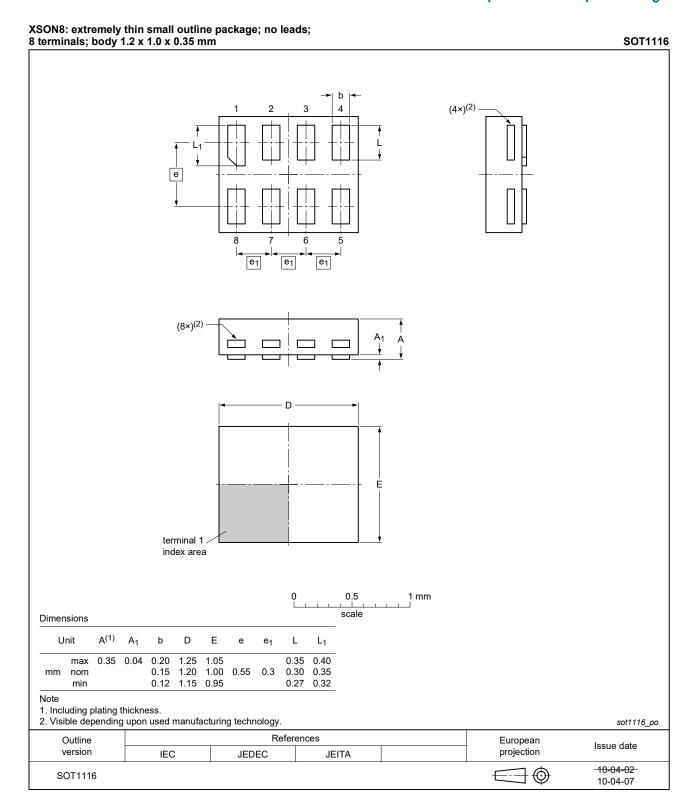


Fig. 8. Package outline SOT1116 (XSON8)

Low-power dual 2-input NAND gate

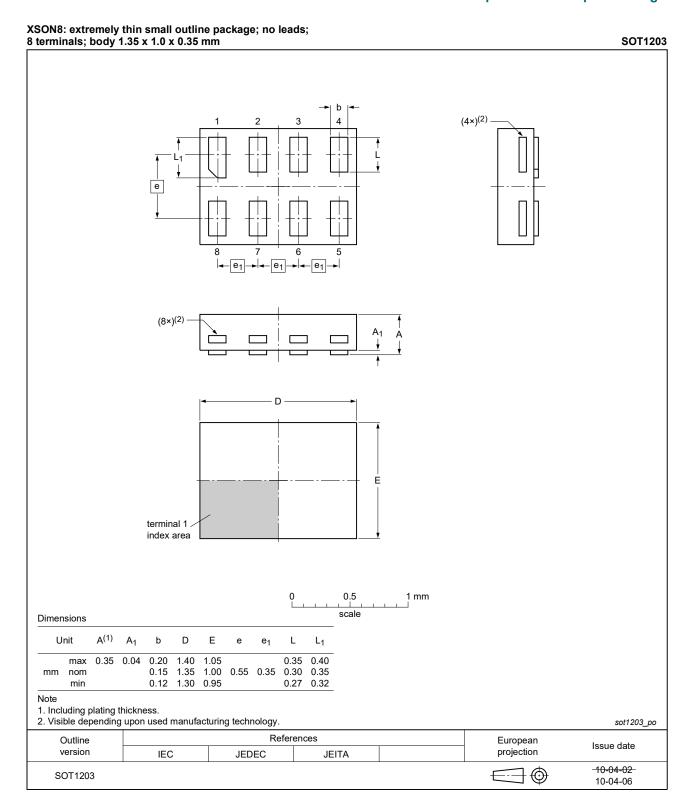


Fig. 9. Package outline SOT1203 (XSON8)

Product data sheet

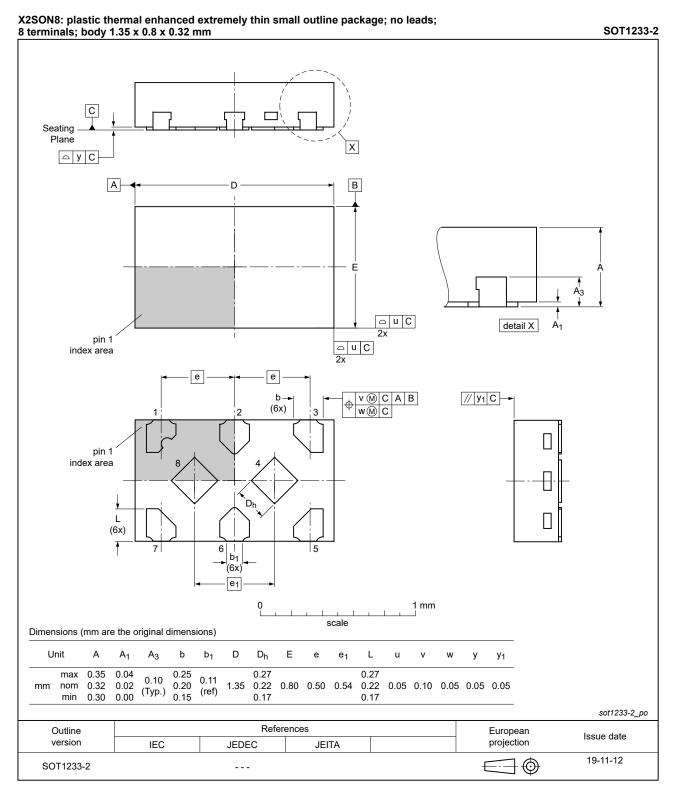


Fig. 10. Package outline SOT1233-2 (X2SON8)

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13. Abbreviations

Table 11. Abbreviations

Acronym	Description
ANSI	American National Standards Institute
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
ESDA	ElectroStatic Discharge Association
НВМ	Human Body Model
JEDEC	Joint Electron Device Engineering Council

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G00 v.14	20240812	Product data sheet	-	74AUP2G00 v.13
Modifications:	Type number	r 74AUP2G00GM (SOT	902-2/XQFN8) remo	oved.
74AUP2G00 v.13	20240416	Product data sheet	-	74AUP2G00 v.12
Modifications:	Type number	r 74AUP2G00GF (SOT	1089/XSON8) remov	/ed.
74AUP2G00 v.12	20230714	Product data sheet	-	74AUP2G00 v.11
Modifications:	<u>Section 2</u> : Es	SD specification update	d according to the la	test JEDEC standard.
74AUP2G00 v.11	20220609	Product data sheet	-	74AUP2G00 v.10
Modifications:		ating values for P _{tot} tota 2SON8) package chang	•	•
74AUP2G00 v.10	20170703	Product data sheet	-	74AUP2G00 v.9
	• <u>Section 6.1</u> a	ave been adapted to th and <u>Fig. 10</u> (drawings So r 74AUP2G00GD remov	OT1233/X2SON8) u	
74AUP2G00 v.9	20161028	Product data sheet	-	74AUP2G00 v.8
Modifications:	Added type r	number 74AUP2G00GX	(SOT1233/X2SON	3)
74AUP2G00 v.8	20130205	Product data sheet	-	74AUP2G00 v.7
Modifications:	For type num	nber 74AUP2G00GD X	SON8U has changed	to XSON8.
74AUP2G00 v.7	20120608	Product data sheet	-	74AUP2G00 v.6
74AUP2G00 v.6	20111201	Product data sheet	-	74AUP2G00 v.5
74AUP2G00 v.5	20101021	Product data sheet	-	74AUP2G00 v.4
74AUP2G00 v.4	20080605	Product data sheet	-	74AUP2G00 v.3
74AUP2G00 v.3	20080403	Product data sheet	-	74AUP2G00 v.2
74AUP2G00 v.2	20070515	Product data sheet	-	74AUP2G00 v.1
74AUP2G00 v.1	20060825	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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